TAVAKOL ELECTRONIC
توکل الکترونیک
مرجع تخصصی تأمین قطعات الکترونیکی اورجینال
این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وب‌سایت توکل الکترونیک مراجعه فرمایید.
مشاهده قیمت و خرید
برای خرید و مشاهده سایر محصولات کلیک کنید

SEMIKRON

SKiiP 30 NAB 12 T10

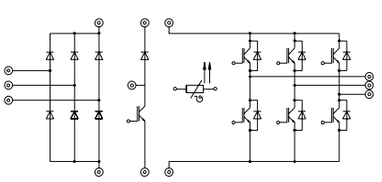
Absolute Maximum Ratings			
Symbol	**Conditions** [1]	**Values**	**Units**
Inverter	(Chopper see SKiiP 22 NAB 12 T18)		
V_{CES}		1200	V
V_{GES}		± 20	V
I_C	$T_{heatsink}$ = 25 / 80 °C	33 / 22	A
I_{CM}	t_p < 1 ms; $T_{heatsink}$ = 25 / 80 °C	66 / 44	A
$I_F = -I_C$	$T_{heatsink}$ = 25 / 80 °C	38 / 26	A
$I_{FM} = -I_{CM}$	t_p < 1 ms; $T_{heatsink}$ = 25 / 80 °C	76 / 52	A
Bridge Rectifier			
V_{RRM}		1500	V
I_D	$T_{heatsink}$ = 80 °C	35	A
I_{FSM}	t_p = 10 ms; sin. 180 °, T_j = 25 °C	700	A
I^2t	t_p = 10 ms; sin. 180 °, T_j = 25 °C	2400	A^2s
T_j		– 40 ... + 150	°C
T_{stg}		– 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics					
Symbol	**Conditions** [1]	**min.**	**typ.**	**max.**	**Units**
IGBT - Inverter					
V_{CEsat}	I_C = 25 A T_j = 25 (125) °C	–	2,5(3,1)	3,0(3,7)	V
$t_{d(on)}$	V_{CC} = 600 V; V_{GE} = ± 15 V	–	75	150	ns
t_r	I_C = 25 A; T_j = 125 °C	–	65	130	ns
$t_{d(off)}$	$R_{gon} = R_{goff}$ = 47 Ω	–	400	600	ns
t_f	inductive load	–	50	100	ns
$E_{on} + E_{off}$		–	6,2	–	mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V, 1 MHz	–	1,65	–	nF
R_{thjh}	per IGBT	–	–	1,0	K/W
IGBT - Chopper *					
V_{CEsat}	I_C = 15 A T_j = 25 (125) °C	–	2,5(3,1)	3,0(3,7)	V
$t_{d(on)}$	V_{CC} = 600 V; V_{GE} = ± 15 V	–	55	110	ns
t_r	I_C = 15 A; T_j = 125 °C	–	45	90	ns
$t_{d(off)}$	$R_{gon} = R_{goff}$ = 82 Ω	–	400	600	ns
t_f	inductive load	–	70	100	ns
$E_{on} + E_{off}$		–	4,0	–	mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V, 1 MHz	–	1,0	–	nF
R_{thjh}	per IGBT	–	–	1,4	K/W
Diode [2] - Inverter (Diode [2] - Chopper see SKiiP 22 NAB 12 T18)					
$V_F = V_{EC}$	I_F = 25 A T_j = 25 (125) °C	–	2,0(1,8)	2,5(2,3)	V
V_{TO}	T_j = 125 °C	–	1,0	1,2	V
r_T	T_j = 125 °C	–	32	44	mΩ
I_{RRM}	I_F = 25 A, V_R = – 600 V	–	25	–	A
Q_{rr}	di_F/dt = – 500 A/µs	–	4,5	–	µC
E_{off}	V_{GE} = 0 V, T_j = 125 °C	–	1,0	–	mJ
R_{thjh}	per diode	–	–	1,2	K/W
Diode - Rectifier					
V_F	I_F = 35 A T_j = 25 °C	–	1,2	–	V
R_{thjh}	per diode	–	–	1,6	K/W
Temperature Sensor					
R_{TS}	T = 25 / 100 °C		1000 / 1670		Ω
Mechanical Data					
M_1	Mounting torque	2	–	2,5	Nm
Case			M3		

MiniSKiiP 3
SEMIKRON integrated intelligent Power
SKiiP 30 NAB 12 T10
3-phase bridge rectifier + braking chopper
3-phase bridge inverter

Case M3





UL recognized file no. E63532

Options

- also available with powerful chopper. For characteristics please refer to Inverter IGBT

[1] $T_{heatsink}$ = 25 °C, unless otherwise specified
[2] CAL = Controlled Axial Lifetime Technology (soft and fast recovery)

* For diagrams of the Chopper IGBT please refer to SKiiP 22 NAB 12 T18

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

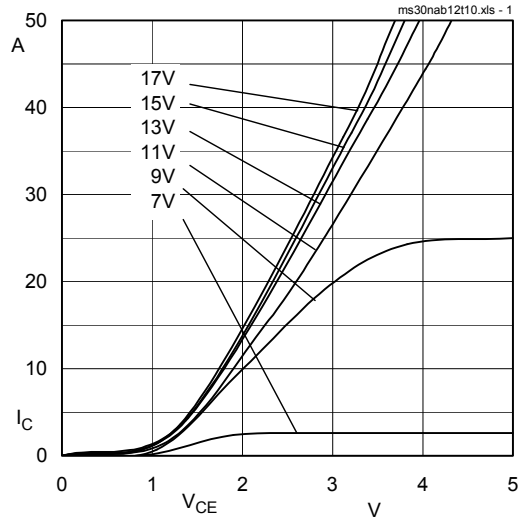


Fig. 1 Typ. output characteristic, t_p = 80 µs; 25 °C

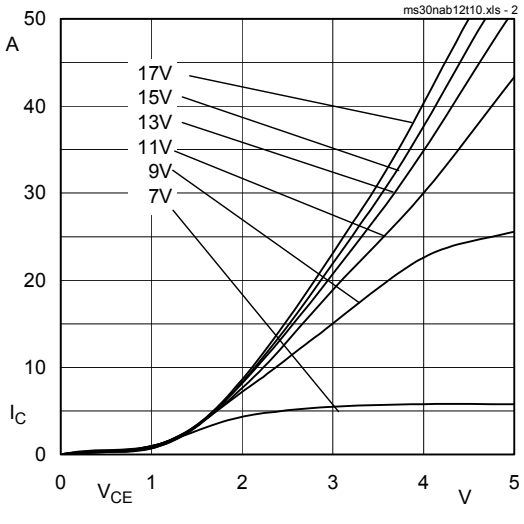


Fig. 2 Typ. output characteristic, t_p = 80 µs; 125 °C

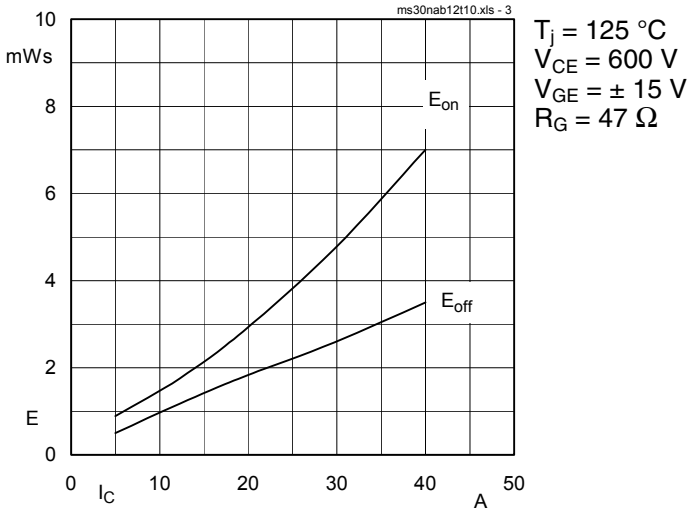


Fig. 3 Turn-on /-off energy = f (I_C)

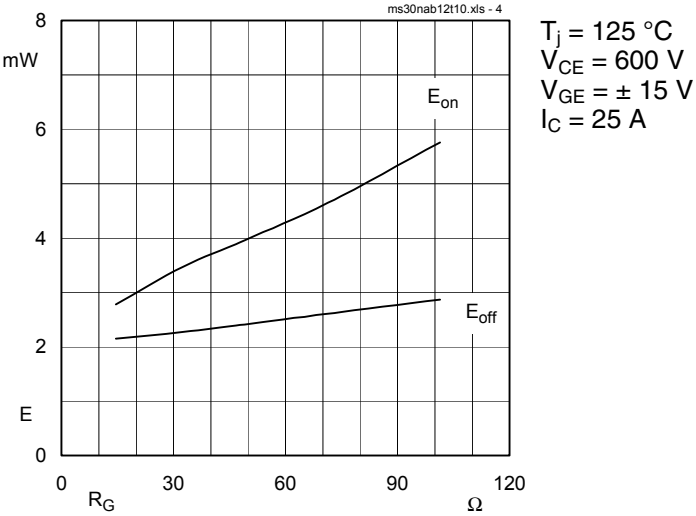


Fig. 4 Turn-on /-off energy = f (R_G)

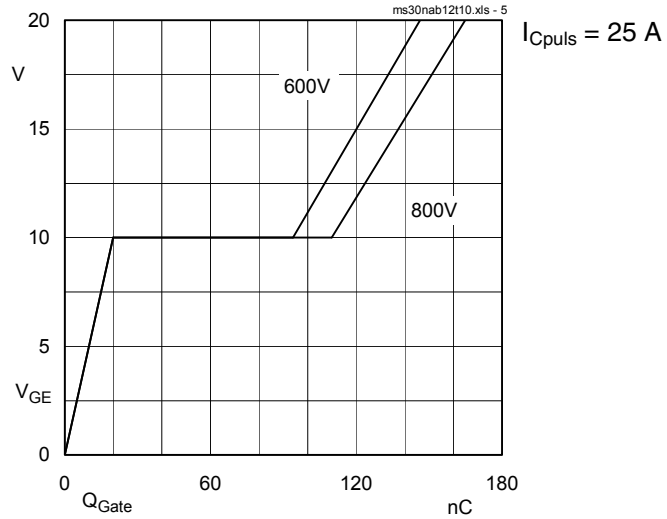


Fig. 5 Typ. gate charge characteristic

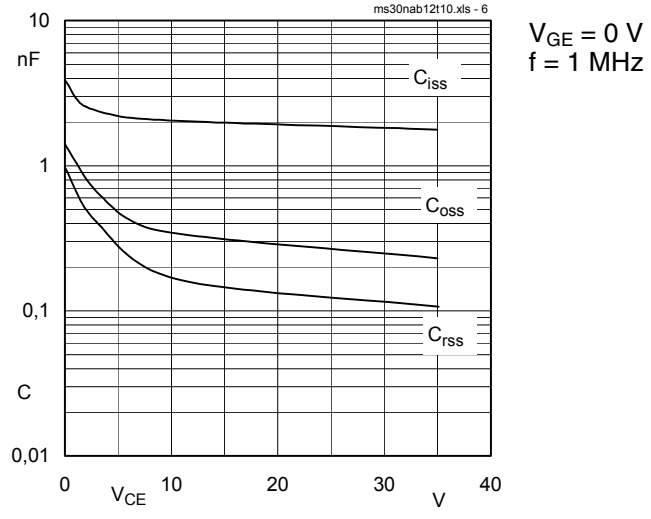


Fig. 6 Typ. capacitances vs. V_{CE}